Silicon Epitaxial Planar Diode

Low leakage switching diode

Features

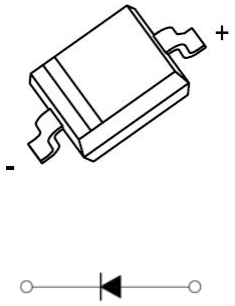
- Plastic SMD package
- Low leakage current

Application

- Low leakage current applications in surface mounted circuits.

MARKING: JV

SOD-323



Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V_{RRM}	85	V
Continuous Reverse Voltage		V_R	75	V
Continuous Forward Current		I_F	200	mA
Repetitive Peak Forward Current		I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	t = 1 µs t = 1 ms t = 1 s	I_{FSM}	4 1 0.5	A
Power Dissipation		P_{tot}	200	mW
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 1 mA at I_F = 10 mA at I_F = 50 mA at I_F = 150 mA	 V_F V_F V_F V_F	 - - - -	 0.9 1 1.1 1.25	 V V V V
Reverse Current at V_R = 75 V at V_R = 75 V, T_j = 150 °C	I_R	 - -	 5 80	nA
Diode Capacitance at V_R = 0, f = 1 MHz	C_d	2	-	pF
Reverse Recovery Time at I_F = I_R = 10 mA, R_L = 100 Ω, i_{rr} = 0.1 I_R	t_{rr}	-	3	µs

Typical Characteristics